

GSDSBAT54 Series

Surface Mount Schottky Barrier Diodes

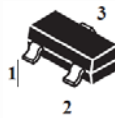
Product Description

Small signal schottky diodes 300mA / 30V.

Features

- Low Turn-on Voltage
- Fast Switching
- PN Junction Guard Ring for Transient
- SOT-23 Package
- Lead(Pb)-Free

Packages



SOT-23

Ordering Information

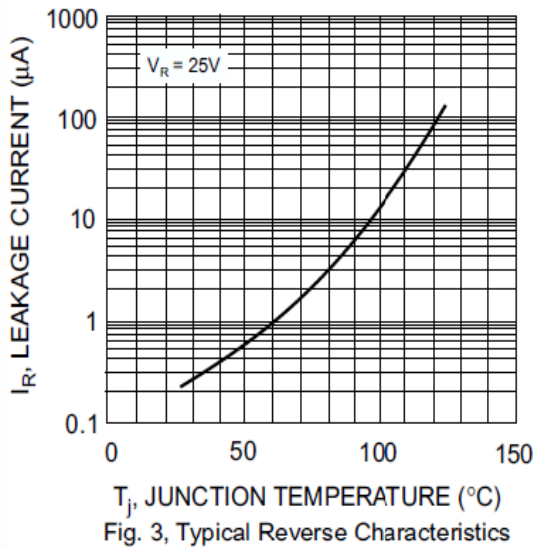
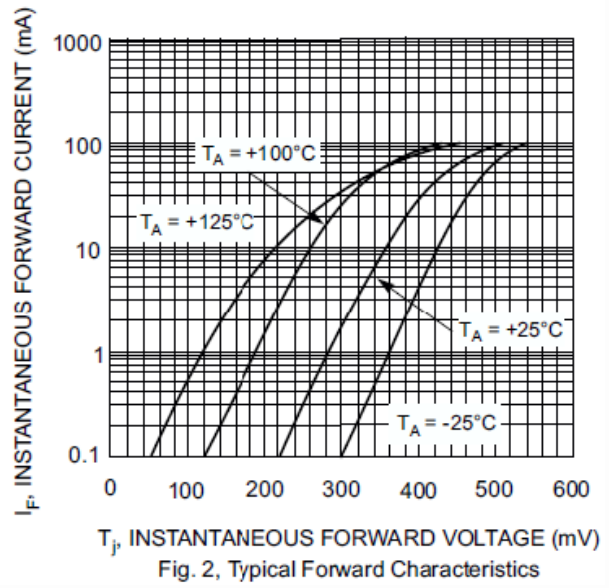
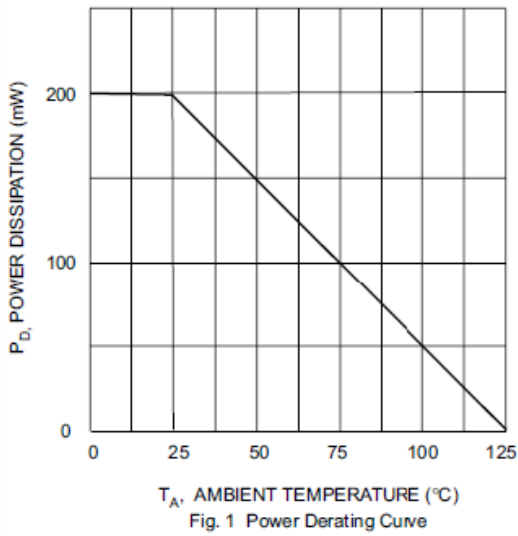
P/N	Package	Equivalent Circuit diagram	Quantity
GSDSBAT54F	SOT-23		3000 PCS
GSDSBAT54CF	SOT-23		
GSDSBAT54AF	SOT-23		
GSDSBAT54SF	SOT-23		

Absolute Maximum Ratings & Electrical Characteristics

(T_A=25°C Unless otherwise noted)

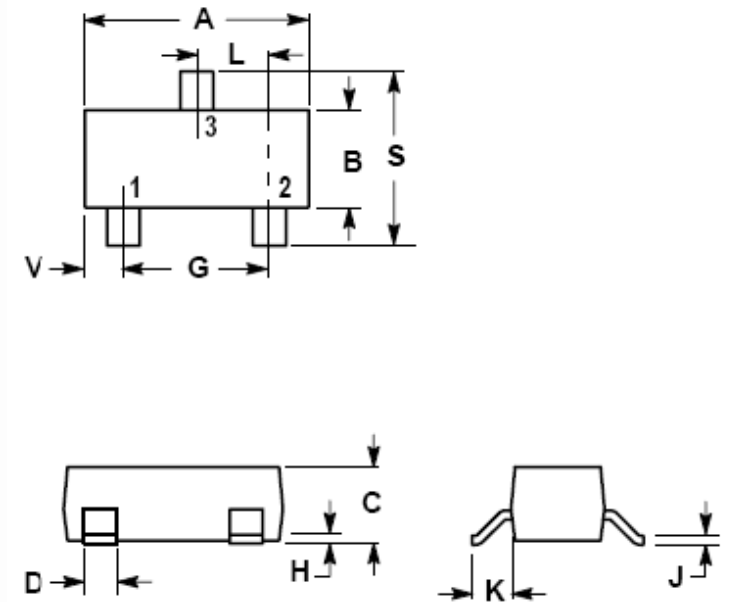
Symbol	Parameter	Value	Unit		
V _{RM}	Reverse Voltage (Repetitive Peak)	30	V		
V _R	Reverse Voltage (DC)	30	V		
I _{FRM}	Repetitive Peak Forward Current	300	mA		
I _{FSM}	Forward current surge peak	600	mA		
T _J	Junction Temperature	125	°C		
T _{STG}	Storage Temperature Range	-65 to +125	°C		
Symbol	Parameter	Min	Typ	Max	Unit
V _F	Forward Voltage (I _F =0.1mA)	-	-	240	mV
	Forward Voltage (I _F =1.0mA)	-	-	320	
	Forward Voltage (I _F =10mA)	-	-	400	
	Forward Voltage (I _F =30mA)	-	-	500	
	Forward Voltage (I _F =100mA)	-	-	1000	
I _R	Reverse Current (V _R =25V)	-	-	2.0	uA

Typical Characteristics



Package Dimension

SOT-23










Dimensions				
Symbol	Millimeters		Inches	
	Min	Max	Min	Max
A	2.80	3.04	0.1102	0.1197
B	1.20	1.40	0.0472	0.0551
C	0.89	1.11	0.0350	0.0440
D	0.37	0.50	0.0150	0.0200
G	1.78	2.04	0.0701	0.0807
H	0.013	0.100	0.0005	0.0040
J	0.085	0.177	0.0034	0.0070
K	0.35	0.69	0.0140	0.0285
L	0.89	1.02	0.0350	0.0401
S	2.10	2.64	0.0830	0.1039
V	0.45	0.60	0.0177	0.0236



NOTICE

Information furnished is believed to be accurate and reliable. However Globaltech Semiconductor assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties, which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of Globaltech Semiconductor. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information without express written approval of Globaltech Semiconductor.

CONTACT US

GS Headquarter	
	4F.,No.43-1,Lane11,Sec.6,Minquan E.Rd Neihu District Taipei City 114, Taiwan (R.O.C)
	886-2-2657-9980
	886-2-2657-3630
	sales_twn@gs-power.com

Shenzhen Branch(China)	
	1113 B Building, Happiness Washington, Baoan Nan Road, Luohu District, Shenzhen City, China
	0755-22208941
	sales_cn@gs-power.com

RD Division	
	824 Bolton Drive Milpitas. CA. 95035
	1-408-457-0587